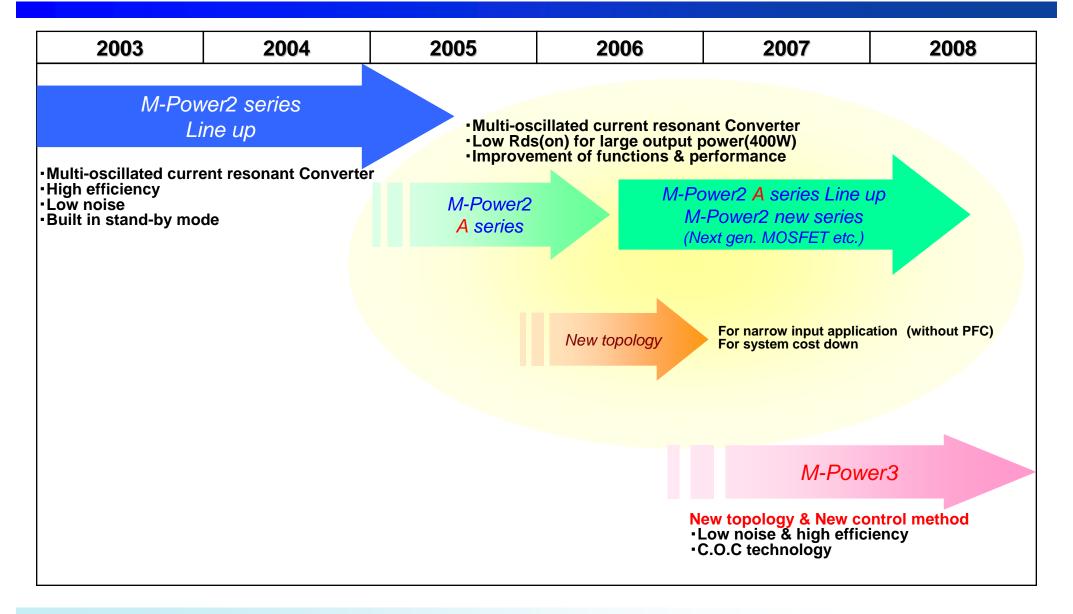


Smart power device M-Power2

Development road map of Fuji M-Power







High efficiency (a reduction in SMPS size is possible.)

DC/DC : 95.3%(DC input:385V,output:24V)

◆ PFC+DC/DC : 88.4%(AC100V),90.7%(AC200V)

Low noise (a reduction in the noise suppression parts is possible.)

MOSFETs:

Turn-on : ZVS+ZCS

◆ Turn-off : ZVS

Diodes (secondary side)

Surge voltage does not occur at reverse recovery.

☐ Fail-safety (Built in protection functions : OC, SC, OV, Tj(OH))

Easy design power supply (Reduction of design time)

Stand-by mode (A series: External, Conventional series: Built in)

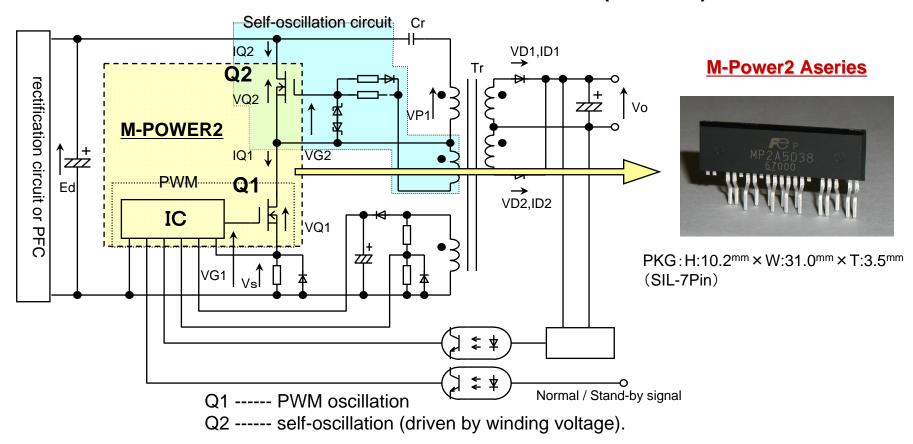
Pin<0.4W at Pout=0.0W</p>

Pin<1.0W at Pout=0.23W</p>

Pin<4.0W at Pout=2.0W</p>



Multi-oscillated current resonant circuit (MOCRC)



Features of the Multi-oscillated current resonant

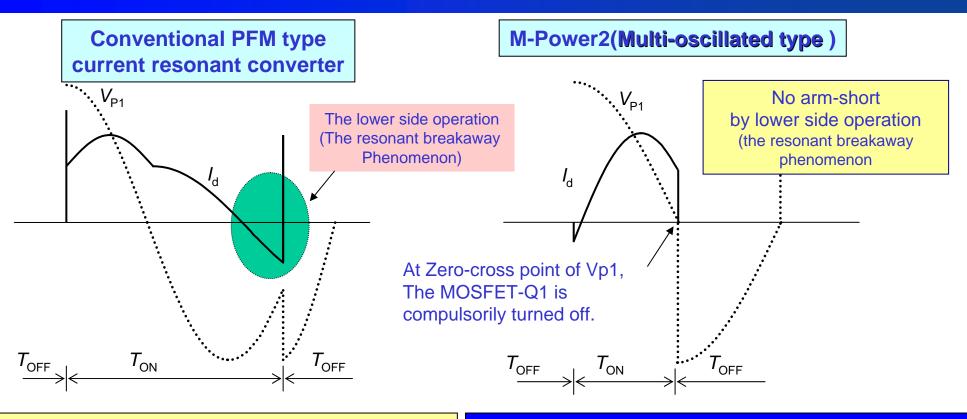
- 1) No arm-short circuit by No lower side operation (No resonant breakaway phenomenon) → Easy to design
- 2) Low noise & high efficiency (at light load too) → same as conventional PFM type or more

Comparison of conventional PFM type and multi-oscillated type(M-Power2)^{nt runners}

	Conventional PFM type	Multi-oscillated type (M-Power2)		
Circuit configuration	HWIC BY BY BY BY BY BY BY BY BY BY BY BY BY			
Gate Driving	HVIC	LVIC+ Trans. winding (high side)		
Control method	PFM(Fixed Duty:50%)	PWM+PFM(variable Duty)		
MOSFET Vds	>500V	>500V		
Efficiency (DC/DC)	>92-93%	>93-95%		
Noise	Low	Low		
Loss at no load	>3W	< 0.4W		
Size	0	⊚ (Built-in standby mode)		
Design	Difficult	Easy to do fail-safety design		

Operation of switching transient





There is a possibility that the lower side operation (the resonant breakaway phenomenon) happens. In the condition of a low input voltage and the overload, when the drain current of Low side MOSFET(Q1) becomes minus, Upperside MOSFET(Q2) turn on and body diode of Q1 operates high – di/dt reverse recovery and the arm-short happens. In the worst case, MOSFET(Q1) is destroyed.

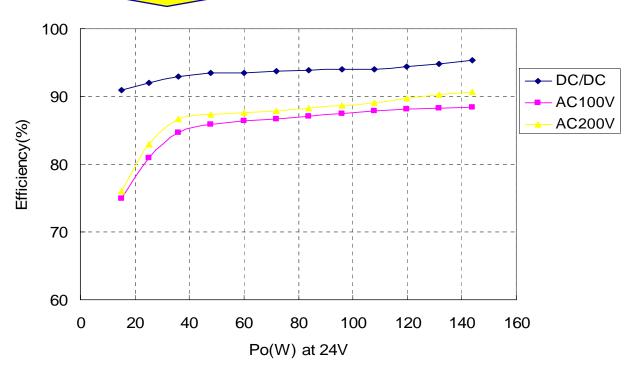
M-Power2 always detects winding voltage(Vp3) and has the function of turning off MOSFET(Q1) at Zero-cross point of Vp3(Vp1). The phase of the voltage is later for that of the current (about 90deg.).

So the drain current of Low side MOSFET(Q1) is always plus and the lower side operation (resonant breakaway phenomenon) never happen.

It is easy to do fail-safety design.



High efficiency



DC/DC : 95.3%

(DC input:385V,output:24V)

PFC+DC/DC:88.4%(AC100V)

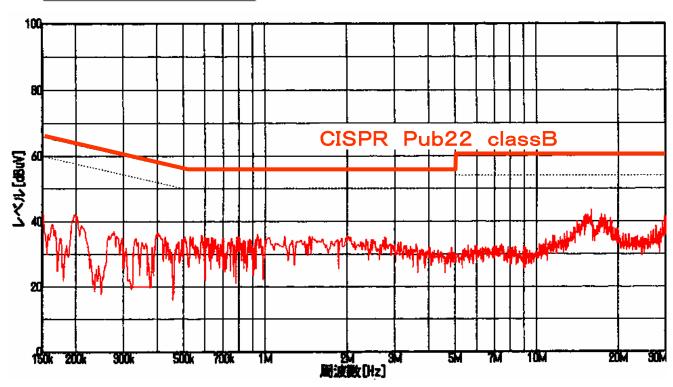
90.7%(AC200V)

Efficiency - Load characteristic at normal mode

Down size your SMPS

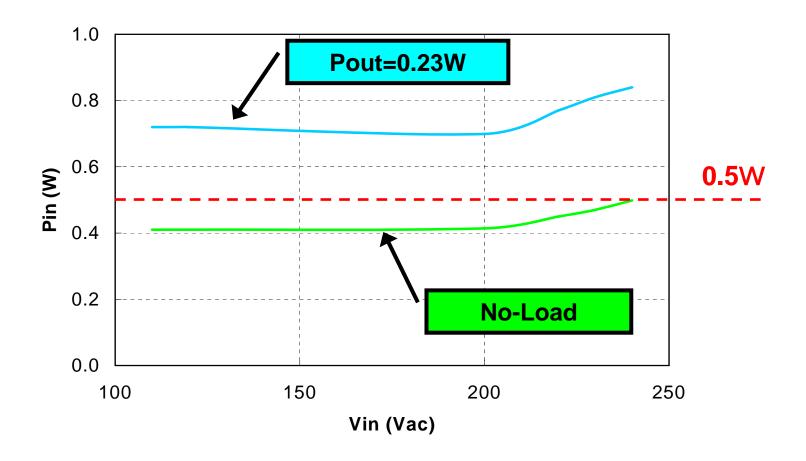


Conducted Emission





- Input power is less than 0.9W at the output power is 0.23W (5V/46mA).
- Input power is less than 0.5W at the No-load.





♦ Line up of M-Power2 A series

Type name	MOSFET(Q1)		MOSFET(Q2)		Control IC		Commis
	V DS	R DS(ON)	V DS	R DS(ON)	V CC(ON)	Т j(ОН)	Sample
MP2A5038	500V	0.38Ω	500V	0.38Ω	16.5V	125 ~ 150 ℃	M/P
MP2A5060	500V	0.6Ω	500V	0.6Ω			M/P
MP2A5077	500V	0.77Ω	500V	0.77Ω			Apr2007
MP2A5100	500V	1Ω	500V	1Ω			May-07
MP2A5135	500V	1.35Ω	500V	1.35Ω			May-07
MP2A2010	250V	0.1Ω	250V	0.1Ω			Apr2007
MP2A2013	250V	0.125Ω	250V	0.125Ω			Apr2007

◆ Line up of M-Power2 (Conventional series)

Type name	MOSFET(Q1)		MOSFET(Q2)		Control IC		Sample
	V DS	R DS(ON)	V DS	R DS(ON)	V CC(ON)	Т j(ОН)	Sample
F9220L	500V	0.93Ω	500V	0.93Ω	16.5V 125 ~ 150 ℃		M/P
F9222L	500V	0.6Ω	500V	0.6Ω			M/P
F9223L	500V	0.5Ω	500V	0.5Ω		M/P	
F9231L	250	0.125Ω	250V	0.125Ω			M/P



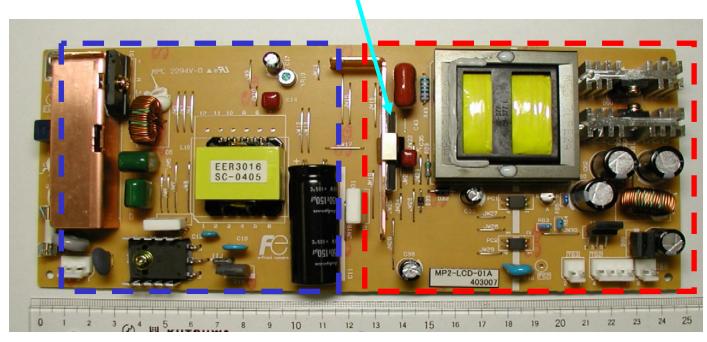
M-Power2

Spec.

Input:AC90~264V Output:150W 24V/6A 5V/1.2A

Outline

W:246mm D:100mm **H:20mm**



PFC circuit (CDM)

Multi-oscillated current resonant converter

